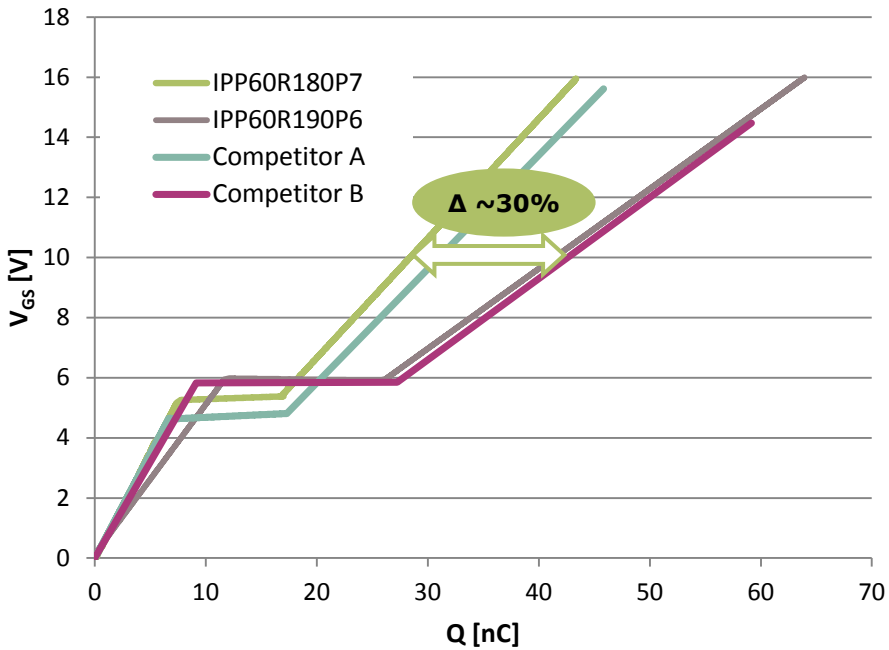
600 V CoolMOS™ P7 for high power SMPS

Tamara Krappinger

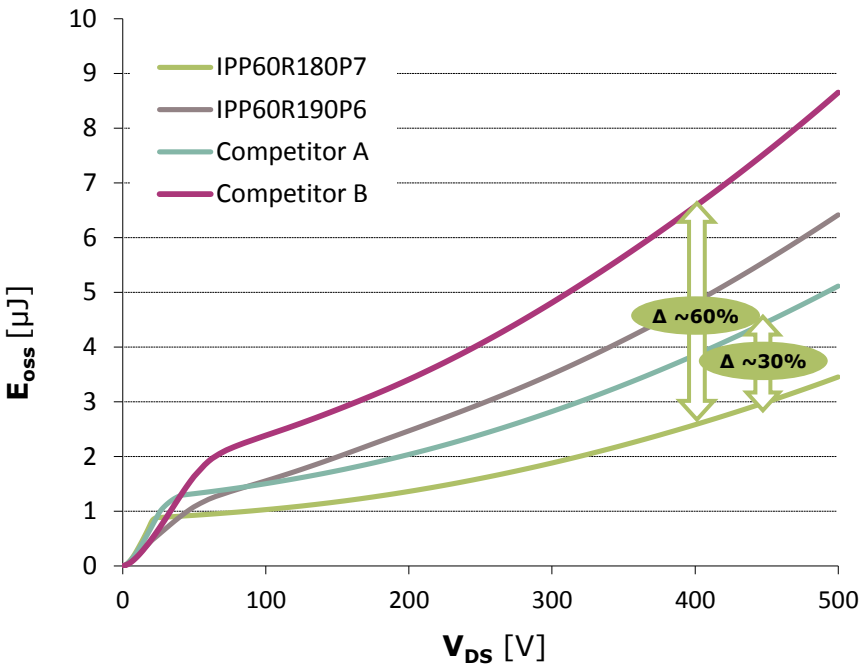
July 2017

600 V CoolMOS™ P7 offers significant reduction of driving and switching losses

1 Driving losses (Q_G)



2 Switching losses (E_{oss})



600 V CoolMOS™ P7 offers

- ~30% reduced gate charge over competition at 10 V
- between 30% and 60% lower E_{oss} than competition at 400 V

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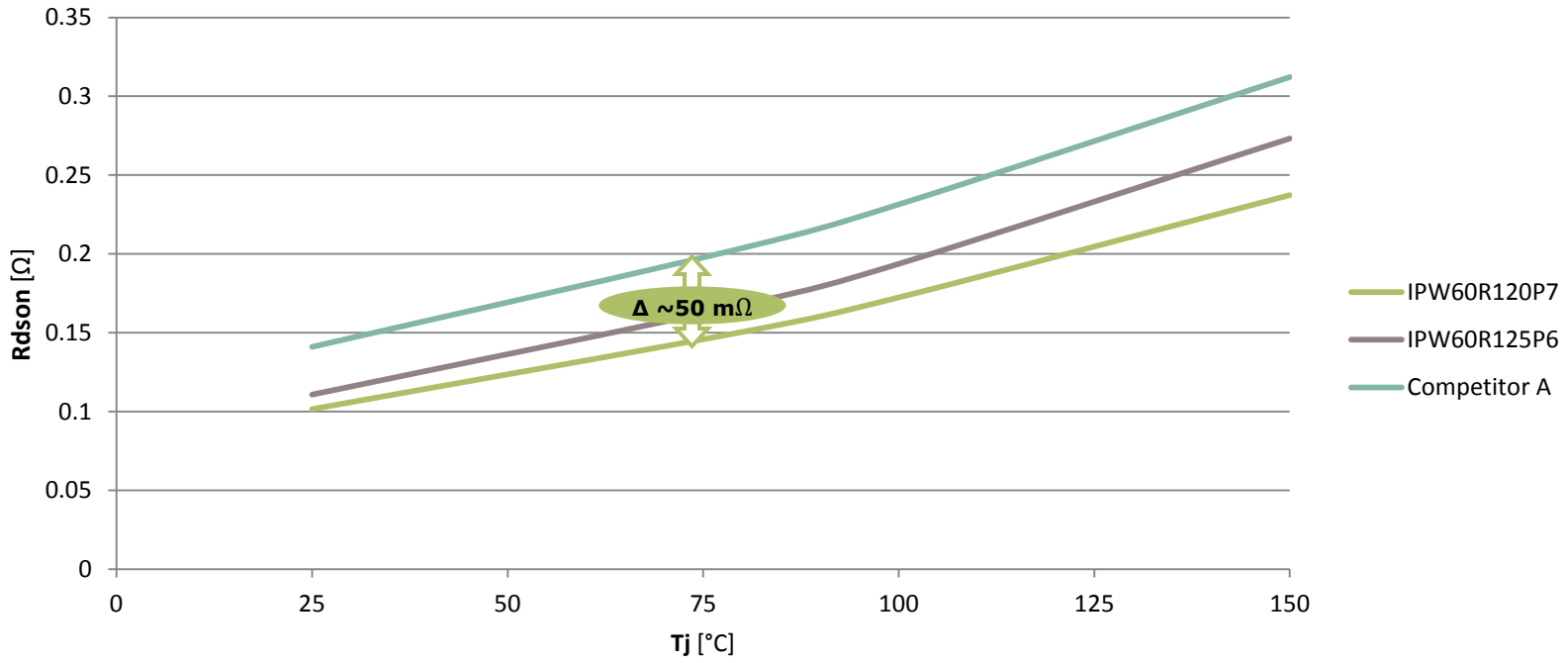
600 V CoolMOS™ P7 offers significant reduction of conduction losses

Rdson[Ω] at 10 A over Tj [°C]



CoolMOS™ P7 600 V offers a lower typical $R_{DS(on)}$ than competitor offerings leading to a reduction of conduction losses

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